

**DETAILED ACTION**

**EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it **MUST** be submitted no later than the payment of the issue fee.

The application has been amended as per telephone authorization from applicant's attorney James Judge on 01/14/2010 as follows:

- In line 3 of claim 12, after "a step of growing", --simultaneously -- has been inserted.
- Canceled withdrawn claims 22-27 (Election without traverse).

***Allowable Subject Matter***

2. Claims 12-21, 28-31 are allowed.

The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record fails to teach or suggest a method of manufacturing a Group III nitride semiconductor device particularly with a step of growing simultaneously at least two Group III nitride semiconductor crystal substrates of semiconductor-device-scale dimension on a starting substrate; a step of growing

at least one device forming Group III nitride semiconductor crystal layer on each said Group III nitride semiconductor crystal substrate as set forth in the combination of claim 12.

The dependent claims are allowable at least for the same reason.

Any comments considered necessary by applicant must be submitted no later than the payment of issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

### ***Conclusion***

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure:
  - US-6,617,261: The invention teaches related method of manufacturing a Group III nitride semiconductor device yet fail to teach or suggest a step of growing simultaneously at least two Group III nitride semiconductor crystal substrates of semiconductor-device-scale dimension on a starting substrate; a step of growing at least one device forming Group III nitride semiconductor crystal layer on each said Group III nitride semiconductor crystal substrate as in the claimed device.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to SELIM AHMED whose telephone number is (571)270-5025. The examiner can normally be reached on 9:00 AM-6:00 PM. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue Purvis can be reached on (571)272-1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/SA/

/Sue A. Purvis/  
Supervisory Patent Examiner, Art Unit 2826